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**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

**Applicant: Diane C. Boyd, et al.**

**Docket: 16890**

**Patent No: 7,075,150**

**Dated: August 04, 2006**

**Issued: July 11, 2006**

**For: ULTRA-THIN SI CHANNEL MOSFET  
USING A SELF-ALIGNED OXYGEN IMPLANT  
AND DAMASCENE TECHNIQUE**

**Commissioner of Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450**

**REQUEST FOR CERTIFICATE OF CORRECTION**

**Sir:**

**It appearing that errors have been introduced in the course  
of printing the Patent issued in the above application, it is respectfully  
requested that the Commissioner issue a Certificate of Correction in  
the following respects:**

**Column 12, Line 45, Claim 2:**

**"50.0 mn" should read -- 50.0 nm --**

**Column 12, Line 54, Claim 6:**

**"The semiconducting" should read -- The semiconducting --**

**Certificate  
AUG 22 2006  
of Correction**

**AUG 23 2006**

**Column 12, Line 58, Claim 7:**

**"comrpriase a doped region of sai SOI layer"**

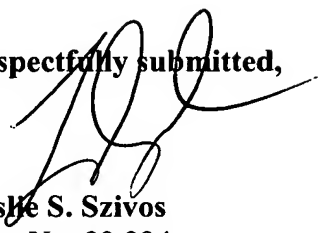
**should read**

**-- comprise a doped region of said SOI layer --**

**Column 13, Line 5, Claim 11:**

**"uried sinsulating" should read -- buried insulating --**

**Respectfully submitted,**



**Leslie S. Szivos  
Reg. No. 39,394**

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**UNITED STATES PATENT AND TRADEMARK OFFICE  
CERTIFICATE OF CORRECTION**

PATENT NO : 7,075,150  
APPLICATION NO : 10/725,849  
ISSUE DATE : July 11, 2006  
INVENTOR(S) : Diane C. Boyd, et al.

It is certified that an error appears or errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

**Column 12, Line 45, Claim 2:**

**"50.0 mn" should read -- 50.0 nm --**

**Column 12, Line 54, Claim 6:**

**"The semiconducting" should read -- The semiconducting --**

**Column 12, Line 58, Claim 7:**

**"comprise a doped region of sai SOI layer"**

**should read**

**-- comprise a doped region of said SOI layer --**

**Column 13, Line 5, Claim 11:**

**"uried sinsulating" should read -- buried insulating --**

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PATENT No. 7,075,150

No. of additional copies

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**AUG 23 2006**